

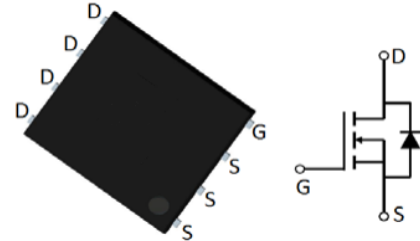
Features

- N-Channel, Low $R_{DS(on)}$ @ $V_{GS}=10V$
- 10V Logic Level Control
- 100% UIS Tested
- Pb-Free, RoHS Compliant

$V_{(BR)DSS}$	$R_{DS(ON)}$ Typ	I_D Max
150V	32mΩ @ 12V	27A
	33mΩ @ 10V	

Applications

- Secondary synchronus rectifier
- Load Switch
- LED backlighting
- Industrial power supplies



Order Information

Product	Package	Marking	Packing
SI7430DP-T1-GE3-CN	PDFN5X6	320N15	4000PCS/Reel

PDFN5X6

Absolute Maximum Ratings

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Symbol	Parameter		Rating	Unit
Common Ratings (T _J =25°C Unless Otherwise Noted)				
V _{GS}	Gate-Source Voltage		±20	V
V _{(BR)DSS}	Drain-Source Breakdown Voltage		150	V
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-50 to 150	°C
Mounted on Large Heat Sink				
I _{DM}	Pulse Drain Current Tested①	T _C =25°C	78	A
I _S	Diode continuous forward current	T _C =25°C	27	A
I _D	Continuous Drain Current	T _C =25°C	27	A
		T _C =70°C	21.6	
P _D	Maximum Power Dissipation	T _C =25°C	62.5	W
EAS	Avalanche energy, single pulsed ②		117.6	mJ
R _{θJC}	Thermal Resistance-Junction to Case		2	°C/W

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ T _J = 25°C (unless otherwise stated)						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V I _D =250μA	150	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current(T _C =25°C)	V _{DS} =120V, V _{GS} =0V	--	--	1	μA
	Zero Gate Voltage Drain Current(T _C =125°C)	V _{DS} =120V, V _{GS} =0V	--	--	100	uA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V	--	--	±100	nA
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	2.0	3.0	4.0	V
R _{DS(ON)}	Drain-Source On-State Resistance③	V _{GS} =12V, I _D =20A	--	32	40	mΩ
R _{DS(ON)}	Drain-Source On-State Resistance③	V _{GS} =10V, I _D =20A	--	33	40	mΩ
Dynamic Electrical Characteristics @ T _J = 25°C (unless otherwise stated)						
C _{iss}	Input Capacitance	V _{DS} =75V, V _{GS} =0V, f=1MHz	--	2294	--	pF
C _{oss}	Output Capacitance		--	101	--	pF
C _{rss}	Reverse Transfer Capacitance		--	5.8	--	pF
R _g	Gate Resistance	f=1MHz		12		Ω
Q _g	Total Gate Charge	V _{DS} =75V I _D =20A, V _{GS} =10V	--	30.5	--	nC
Q _{gs}	Gate Source Charge		--	7.3	--	nC
Q _{gd}	Gate Drain Charge		--	3.9	--	nC
Switching Characteristics @ T _J = 25°C (unless otherwise stated)						
t _{d(on)}	Turn on Delay Time	V _{DD} =75V, I _D =5A, R _G =3.3Ω, V _{GS} =10V	--	29	--	ns
t _r	Turn on Rise Time		--	15	--	ns
t _{d(off)}	Turn Off Delay Time		-	9	--	ns
t _f	Turn Off Fall Time		--	4.2	--	ns
Source Drain Diode Characteristics @ T _J = 25°C (unless otherwise stated)						
t _{rr}	Reverse Recovery Time	I _{SD} =20A, V _{GS} =0V di/dt=500A/μs	--	59	--	nS
Q _{rr}	Reverse Recovery Charge		--	445	--	nC
V _{SD}	Forward on voltage③	I _{SD} =20A, V _{GS} =0V	--	0.86	1.2	V

Notes: ① Pulse width limited by maximum allowable junction temperature

② Limited by T_{Jmax}, starting T_J = 25°C, L = 0.3mH, R_G = 25Ω, I_{AS} = 28A, V_{GS} = 10V. Part not recommended for use above this value

③ Pulse width ≤ 300μs; duty cycle ≤ 2%.

Typical Characteristics

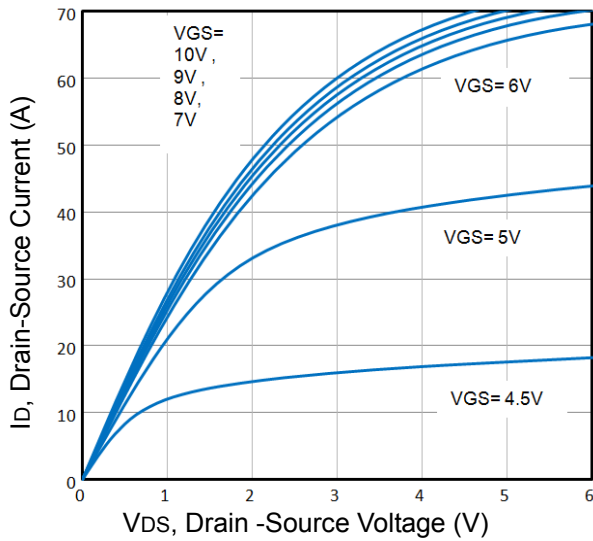


Fig1. Typical Output Characteristics

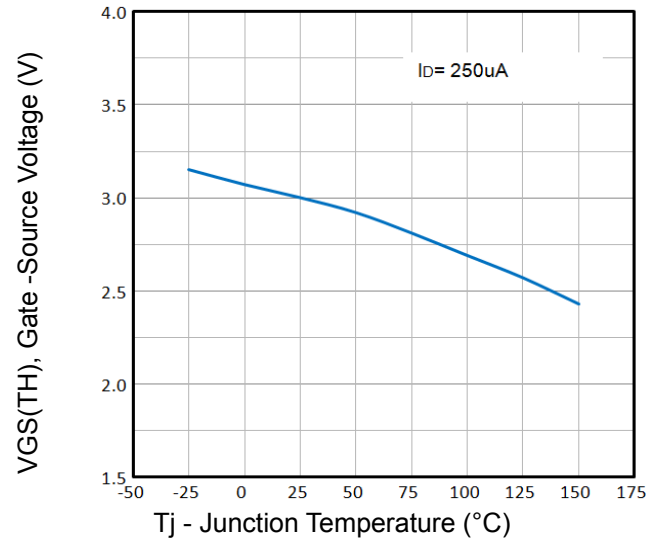


Fig2. Normalized Threshold Voltage Vs. Temperature

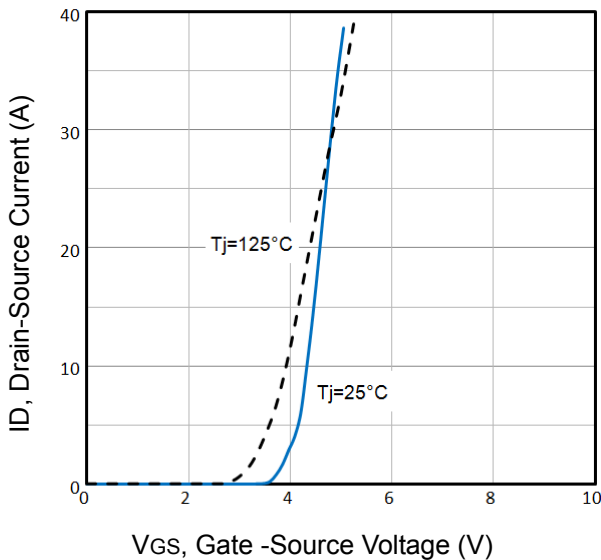


Fig3. Typical Transfer Characteristics

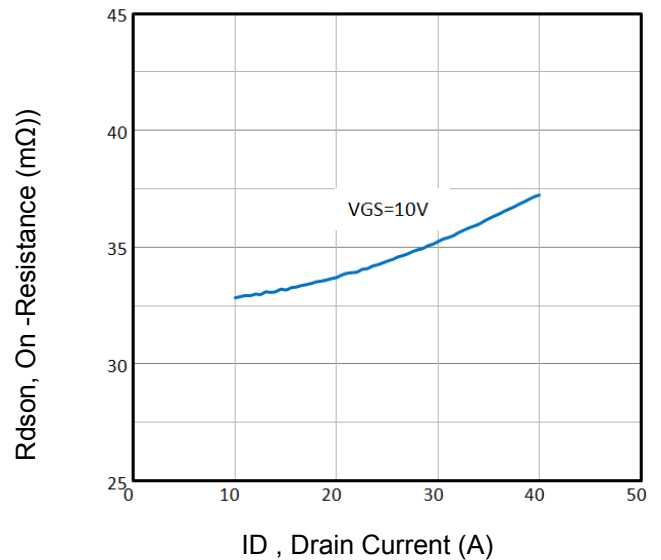


Fig4. On-Resistance vs. Drain Current and Gate Voltage

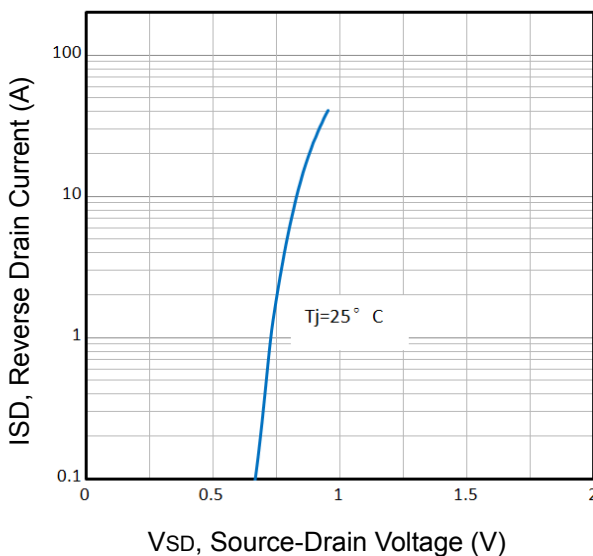


Fig5. Typical Source-Drain Diode Forward Voltage

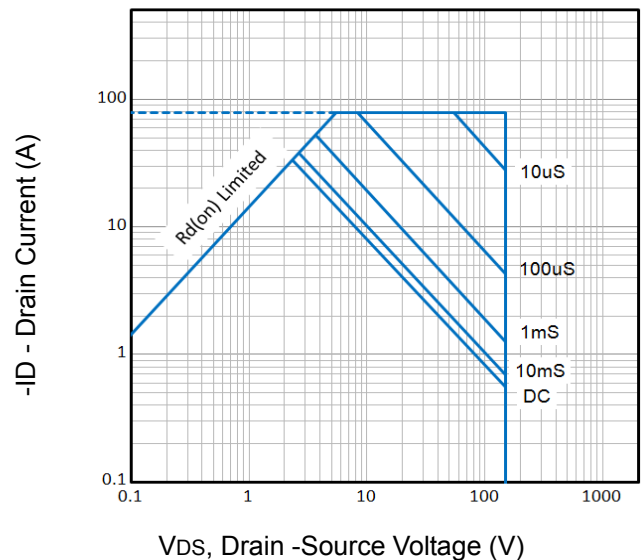


Fig6. Maximum Safe Operating Area

Typical Characteristics

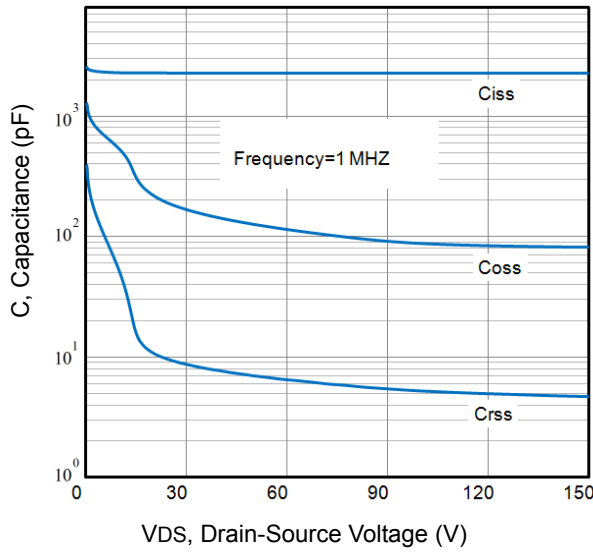


Fig7. Typical Capacitance Vs. Drain-Source Voltage

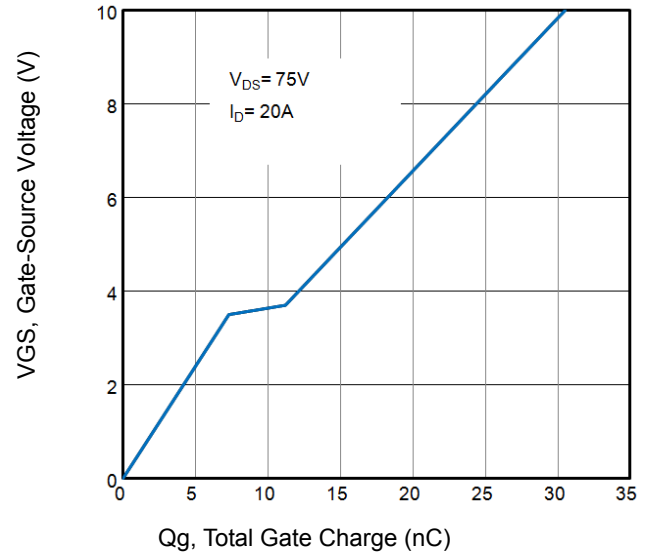


Fig8. Typical Gate Charge Vs. Gate-Source Voltage

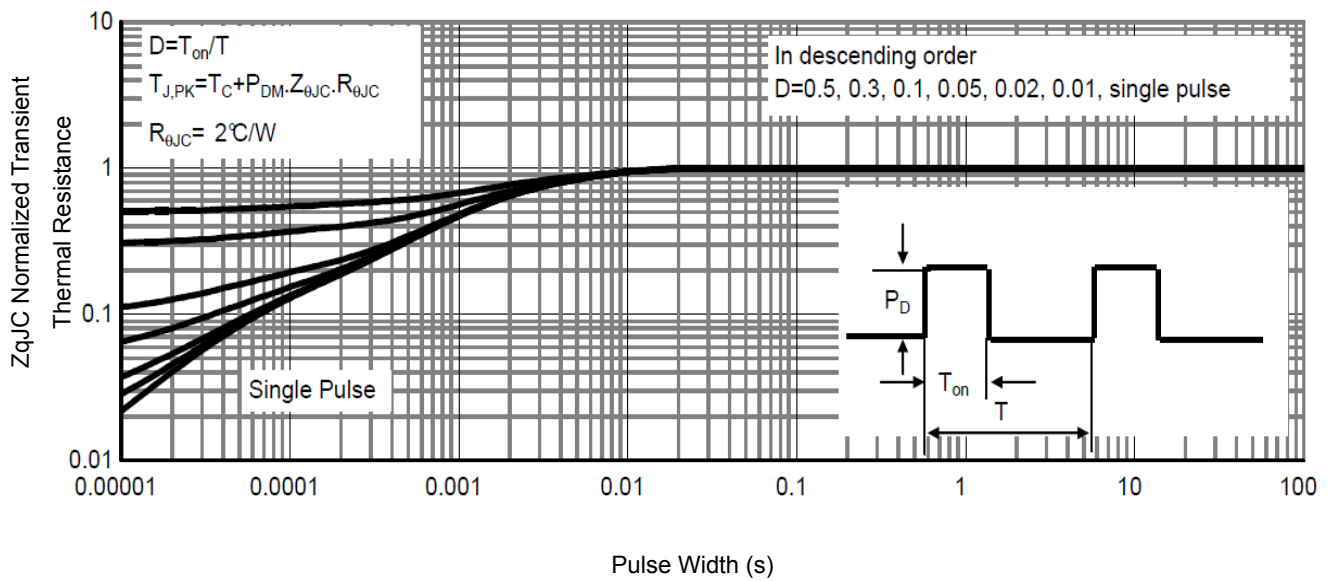


Fig9. Normalized Maximum Transient Thermal Impedance

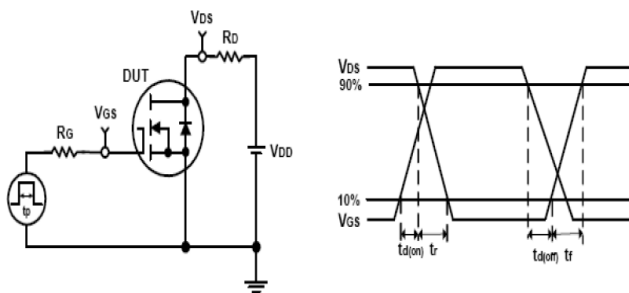


Fig10. Switching Time Test Circuit and waveforms

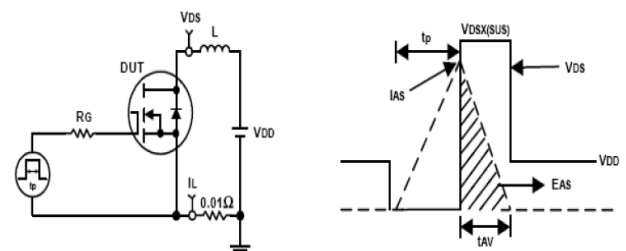
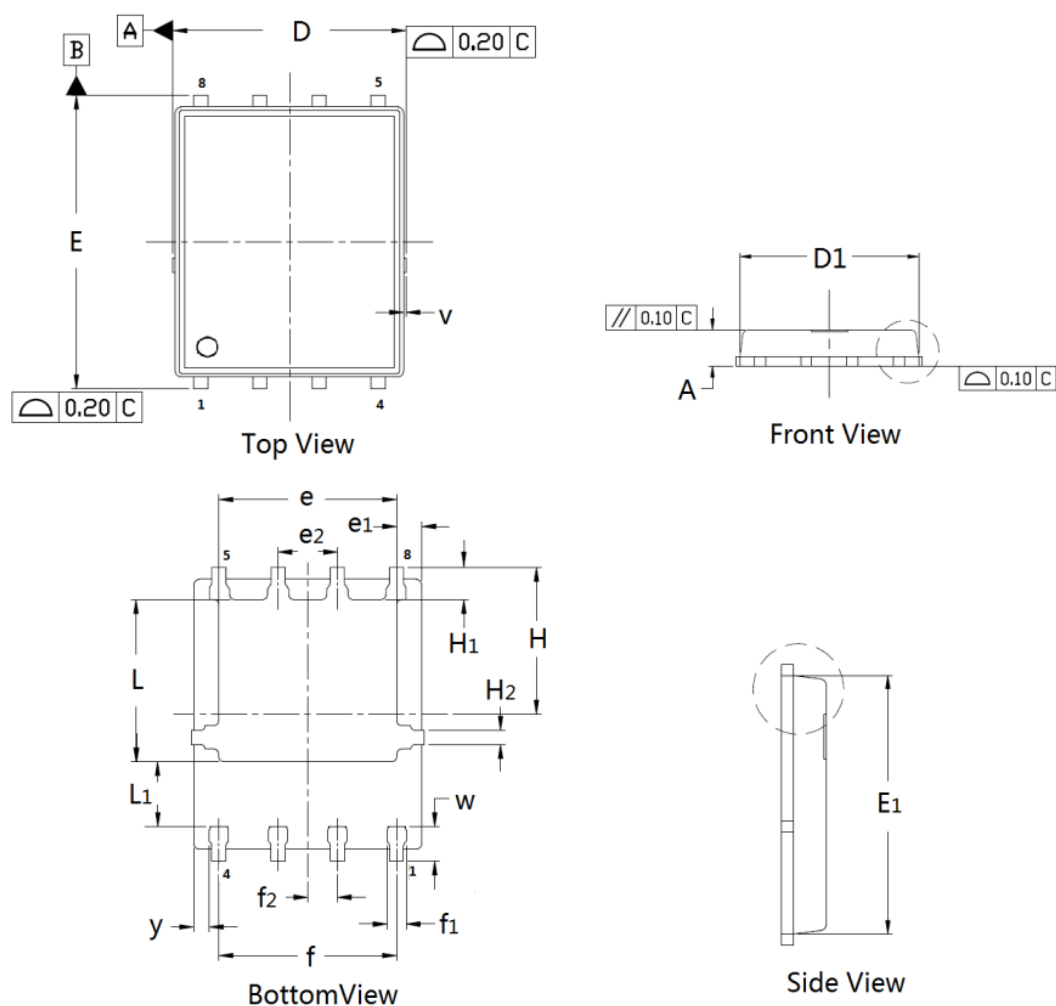


Fig11. Unclamped Inductive Test Circuit and waveforms

PDFN5X6 Mechanical Data

DIMENSIONS (unit : mm)

Symbol	Min	Typ	Max	Symbol	Min	Typ	Max
A	0.90	1.02	1.10	D	4.90	4.98	5.10
D1	4.80	4.89	5.00	E	6.00	6.11	6.20
E1	5.65	5.74	5.85	e	3.72	3.80	3.92
e1	--	0.54	--	e2	--	1.27	--
f	--	3.82	--	f1	0.31	0.37	0.51
f2	--	0.64	--	H	--	3.15	--
H1	0.59	0.63	0.79	H2	0.26	0.28	0.32
L	3.38	3.45	3.58	L1	--	1.39	--
v	--	0.13	--	w	0.64	0.68	0.84
y	--	0.34	--		--		--

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